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To: Assistant Commissioner for Patents **From:** David Bonham
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Fax: 703-872-9318 **Total pages:** 10

Phone: **Date:** 11/22/02

In connection with prosecution in Serial No.
Re: 09/881,254, please find enclosed a Response to **CC:**
the Office Action mailed July 22, 2002.

Sincerely,

David Bonham

Urgent For Review Please Comment Please Reply Please Recycle

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Robertson
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Serial No. 09/881,254

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

Applicant: Fwu-Juan Hshieh et al.

Serial No.: 09/881,254 /

Filed: 06/14/2001

Title: SYMMETRIC TRENCH MOSFET DEVICE AND METHOD OF
MAKING SAME

Art Unit: 2826

Examiner: Mondt, Johanees P.

Docket No.: GS 134

FAX RECEIVEDVIA FACSIMILE 703-872-9318
Assistant Commissioner for Patents
Washington, D.C. 20231

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AMENDMENT AND RESPONSE110.00 CH
Sir:

Responsive to the outstanding Office Action dated July 22, 2002 in the above-identified patent application, please enter the following amendments and remarks:

IN THE CLAIMS:**Please add new claims 25 and 26 as follows:**

25. (Newly added) The trench MOSFET transistor device of claim 1, wherein said trench MOSFET transistor device comprises a plurality of source regions which are shorted to one another.

26. (Newly added) The trench MOSFET transistor device of claim 14, wherein said trench MOSFET transistor device comprises a plurality of source regions which are shorted to one another.